

# Maria Rodriguez

## List of Publications by Year in descending order

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21  
papers

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citations

1478505

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h-index

1372567

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21  
all docs

21  
docs citations

21  
times ranked

326  
citing authors

#	ARTICLE	IF	CITATIONS
1	Advanced processing for mobility improvement in 4H-SiC MOSFETs: A review. Materials Science in Semiconductor Processing, 2018, 78, 22-31.	4.0	80
2	Synchronous Boost Converter With High Efficiency at Light Load Using QSW-ZVS and SiC mosfets. IEEE Transactions on Industrial Electronics, 2018, 65, 386-393.	7.9	39
3	Auxiliary power supply based on a modular ISOP flyback configuration with very high input voltage. , 2016, , .		22
4	High-Voltage 4H-SiC Power MOSFETs With Boron-Doped Gate Oxide. IEEE Transactions on Industrial Electronics, 2017, 64, 8962-8970.	7.9	19
5	High-accuracy modelling of ZVS energy loss in advanced power transistors. , 2018, , .		15
6	Improving the Efficiency of SiC-Based Synchronous Boost Converter Under Variable Switching Frequency TCM and Different Input/Output Voltage Ratios. IEEE Transactions on Industry Applications, 2019, 55, 7757-7764.	4.9	14
7	Different Modular Techniques Applied in a Synchronous Boost Converter With SiC MOSFETs to Obtain High Efficiency at Light Load and Low Current Ripple. IEEE Transactions on Industrial Electronics, 2017, 64, 8373-8382.	7.9	12
8	Series-connected GaN transistors for ultra-fast high-voltage switch (>1kV). , 2017, , .		11
9	SiC-Based High Efficiency High Isolation Dual Active Bridge Converter for a Power Electronic Transformer. Energies, 2020, 13, 1198.	3.1	6
10	Design and construction of a DAB using SiC MOSFETs with an isolation of 24 kV for PET applications. , 2017, , .		5
11	Reliability and Robustness Tests for Next-Generation High-Voltage SiC MOSFETs. IEEE Journal of Emerging and Selected Topics in Power Electronics, 2021, 9, 4320-4329.	5.4	5
12	Discrete-Time Modeling of Pulsewidth Modulated DC-DC Converters in Subsampling Conditions. IEEE Journal of Emerging and Selected Topics in Power Electronics, 2021, 9, 5962-5974.	5.4	5
13	Modelling the performance of a SiC-based synchronous boost converter using different conduction modes. , 2018, , .		4
14	Event-Focused Digital Control to Keep High Efficiency in a Wide Power Range in a SiC-Based Synchronous DC/DC Boost Converter. Electronics (Switzerland), 2020, 9, 2154.	3.1	3
15	Event-focused control strategy for a SiC-based synchronous boost converter working at different conduction modes. , 2018, , .		2
16	Switching performance comparison of a power switch in a cascode configuration using a SuperJunction MOSFET. , 2016, , .		1
17	Novel Selection Criteria of Primary Side Transistors for LLC Resonant Converters. , 2018, , .		1
18	Efficiency evaluation of a SiC-based bidirectional boost converter using TCM-ZVS with different voltage conversion ratios. , 2020, , .		1

#	ARTICLE	IF	CITATIONS
19	Analysis of Intrinsic Switching Losses in Superjunction MOSFETs Under Zero Voltage Switching. Energies, 2020, 13, 1124.	3.1	1
20	Gate impedance characterization and performance evaluation of 3.3kV Silicon Carbide MOSFETs. , 2016, , .		0
21	Two-Domains Control of a Buck Converter. E3S Web of Conferences, 2017, 16, 14005.	0.5	0